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MIPT

$$\Delta E(\mathbf{r}, t) - \mu_0 \varepsilon(\mathbf{r}) \frac{\partial^2}{\partial t^2} E(\mathbf{r}, t) = \mu_0 \frac{\partial^2}{\partial t^2} P_{in}(\mathbf{r}, t)$$
 (1)

Which is solved as

$$E(\mathbf{r},t) = \frac{1}{2}E_0e^{i(\beta y - \omega t)} + \text{const}$$

And we assume:

$$E(\mathbf{r},t) = A(t)E(s').$$

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$$E(\mathbf{r},t) = A(t)E(s'), \tag{2}$$

where A states for for both amplitude and phase. And E(s') eigenmode function.

For most semiconductor lasers waveguides, the lasing action occurs in eigenmode. Also we use slow wave variation.

$$\left| \frac{d^2 A}{dt^2} \right| \ll \omega \left| \frac{dA}{dt} \right|. \tag{3}$$

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$$\frac{dA}{dt} = \frac{i\omega}{2} A \sum_{\alpha} \frac{1}{V(\alpha)} \frac{\int \zeta(\boldsymbol{r},\alpha) |E(s)|^2 ds}{\int \varepsilon(s) |E(s)|^2 ds} \times |\mu(\alpha)|^2 \frac{[\rho_{ee} + \rho_{hh}(\alpha) - 1]}{(E - E_{\alpha}) + iE_{T^2}}, \tag{4}$$

where ρ_{ee} – distribution of electrons, and ρ_{hh} – distribution of holes. It's time to oversimplify this monster:

$$\frac{dA}{dt} = \frac{i\omega}{2\varepsilon n_r^2} A \sum_{\alpha} \Gamma_{MD} \frac{1}{V_{MD}} |\mu(\alpha)|^2 [\rho_{ee} + \rho_{hh} - 1], \qquad (5)$$

where n_r – refractive index of the active region. And Γ_{MD} – dimensional coupling factor that shows how injected carriers interact with photons.

For the most beauty we assume that well is 1D, and the equastion:

$$\frac{dA}{dt} = \frac{1}{2}v_g(\Gamma_{MD}G - i\Gamma_{MD}N_r)A,\tag{6}$$

where $v_q = c/n_r$ is the speed of light in vacuum. And $\Gamma_{MD}G = g$ is so called gain coefficient.

If we obtain photon density inside active region as:

$$P = \frac{1}{2}\varepsilon n_r^2 |AE(0)|^2 / E.$$

And from previous equation we get

$$\frac{dP}{dt} = v_g g p P = v_g \Gamma_{MDGP} = -\gamma_C P + \Gamma g P. \tag{7}$$

And in the same way:

$$\frac{dN}{dt} = -v_g G(E)P = \frac{J}{ed} \left(1 + \frac{\xi P(t-\tau)}{P_0} \right) - \gamma_s N - gP. \quad (8)$$

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$$\frac{dN}{dt} = -v_g G(E)P = \frac{J}{ed} \left(1 + \frac{\xi P(t-\tau)}{P_0} \right) - \gamma_s N - gP. \tag{9}$$

$$\frac{dP}{dt} = v_g g p P = v_g \Gamma_{MDGP} = -\gamma_C P + \Gamma g P. \tag{10}$$

where P – intracavity photon density, N – carrier density, τ – feedback delay time.

And nonlinearities lies in the optical gain function, wich, due to several articles can be explained as:

$$g \approx g_0 g_n (N - N_0) + g_P (P - P_0).$$
 (11)

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Basic scheme¹.

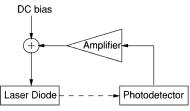


Figure 1: Schematic experimental setup

Laser – single-mode DFB diode (1300 nm);

Light output detector – highspeed InGaAs photodetector;

Important: it is suitable for any other semiconductor laser with an active medium.

¹S. Tang; J.M. Liu, Chaotic Pulsing and Quasi-Periodic Route to Chaos in a Semiconductor Laser with Delayed Opto-Electronic Feedback

The nonlinear behavior of a semiconductor laser with delayed opto-electronic feedback:

$$\frac{dS}{dt} = -\gamma_C S + \Gamma g \, S \qquad S - \text{photon density};$$

$$\frac{dN}{dt} = \frac{J}{ed} - \gamma_s N - g \, S + \frac{J}{ed} \frac{\xi S[t-\tau]}{S_0} \qquad \tau - \text{feedback delay};$$

$$g = g_0 + g_n (N - N_0) + g_p (S - S_0)$$
positive opto-electronic feedback $-\xi > 0$.

Optical gain – measure of how well a medium amplifies photons by stimulated emission.

Laser equations with feedback

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Laser equations with feedback

Some transformations we can reduce this system to the²

$$\frac{ds}{dt} = c_1 n(s+1) - c_2 s(s+1)
\frac{dn}{dt} = c_3 + c_4 s[t-\tau] + (c_5 s - c_8 n)(1+s) - c_6 n - c_7 s,$$

where $s = (S - S_0)/S_0$, $n = (N - N_0)/N_0$, which can be numerically integrated.

²S. Tang; J.M. Liu, Chaotic Pulsing and Quasi-Periodic Route to Chaos in a Semiconductor Laser with Delayed Opto-Electronic Feedback

Numerical solution

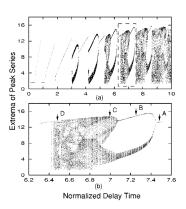


Figure 2: Bifurcation diagram of the extrema of the peak series

Here $\hat{\tau} = \tau f_r$ – demensionless delay.

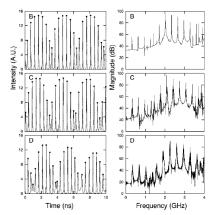


Figure 3: Time series and power spectra

Restoration of the attractor

With part of system variables, it is possible to restore the general view of the attractor.

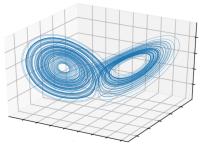


Figure 4: Original system attractor

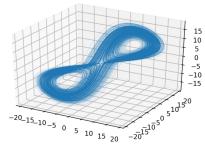


Figure 5: Reconstructed by one coordinate system attractor

Numerical features

Lyapunov exponent:

$$\lambda(x_0) = \lim_{n \to \infty} \frac{1}{n} \sum_{i=0}^{n-1} \ln |f'(x_i)|,$$

where $\lambda > 0$ – characteristic for chaos.

Shannon Entropy:

$$H(X) = -\sum_{i=1}^{n} P(x_i) \log P(x_i),$$

where higher rates correspond to more random sources.

Random number generation.

Random bits produced at a much higher rate than other physical sources of entropy including quantum RNG.

Chaos computing.
It is possible to create
"NOR" gate,
* double-scrolled chaotic
attractor leads to threshold
function.

